

ABSTRACT

An object of the present disclosure is to provide a reflective photomask blank and a reflective photomask
5 having high transferability by making the most use of a phase shift effect. The reflective photomask blank (10) according to an aspect of the present disclosure includes a substrate (1), a reflective layer (2) having a multi-layer film structure, formed on the substrate (1), and
10 configured to reflect an EUV light, a protective layer (3) formed on the reflective layer (2) and configured to protect the reflective layer (2), and an absorption layer (4) formed on the protective layer (3) and configured to absorb the EUV light, in which the absorption layer (4)
15 includes an absorption layer (4a) and an absorption layer (4b) having different functions from each other, and the absorption layer (4) has a phase difference in a range of 190 degrees or more and 270 degrees or less.

20 FIG. 1